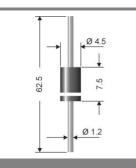
BY 296...BY 299



Axial lead diode

Fast silicon rectifier diodes

BY 296...BY 299

Forward Current: 2 A

Reverse Voltage: 100 to 800 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

- Plastic case DO201
- Weight approx.: 1 g
- Terminals: plated terminals
 solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 1700 pieces per ammo

Valid, if leads are kept at ambient temperature at a distance of 10 mm from case

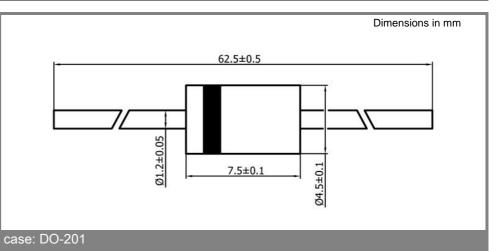
2) I_F = 3 A, T_i = 25 °C

3)
$$T_A = 25 °C$$

٦.	Туре	Repetitive peak	Surge peak	Max. reverse	Max.
		reverse voltage	reverse voltage	recovery time	forward voltage
				I _F = 0,5 A	
				I _R = 1 A	
				I _{RR} = 0,25 A	
		V _{RRM}	V _{RSM}	t _{rr}	
		V	V	ns	V _F ²⁾
	BY 296	100	100	500	1,3
	BY 297	200	200	500	1,3
	BY 298	400	400	500	1,3
	BY 299	800	800	500	1,3

Absolute Maximum Ratings Tc = 25 °C, unless otherwise specified						
Symbol	Conditions	Values	Units			
I _{FAV}	Max. averaged fwd. current, R-load, T _A = 50 °C $^{\rm 1)}$	2	А			
I _{FRM}	Repetitive peak forward current f > 15 Hz ¹⁾	20	А			
I _{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	70	А			
i²t	Rating for fusing, t < 10 ms ³⁾	24	A²s			
R _{thA}	Max. thermal resistance junction to ambient ¹⁾	25	K/W			
R _{thT}	Max. thermal resistance junction to terminals ¹⁾	-	K/W			
T _j	Operating junction temperature	-50+150	°C			
T _s	Storage temperature	-50+175	°C			

Characte	ristics Tc = 25 °C	Tc = 25 °C, unless otherwise specified		
Symbol	Conditions	Values	Units	
I _R	Maximum leakage current, T_j = 25 °C; V_R = V_{RRM}	<10	μA	
	$T_j = °C; V_R = V_{RRM}$			
CJ	Typical junction capacitance	-	pF	
	(at MHz and applied reverse voltage of V)			
Q _{rr}	Reverse recovery charge	-	μC	
	$(U_R = V; I_F = A; dI_F/dt = A/ms)$			
E _{RSM}	Non repetitive peak reverse avalanche energy	-	mJ	
	$(I_R = mA; T_j = °C; inductive load switched off)$			



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